

Junyi Y Zhu

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Gate-tunable room-temperature ferromagnetism in two-dimensional Fe ₃ GeTe ₂ . Nature, 2018, 563, 94-99.	27.8	1,646
2	Quasicrystalline 30° twisted bilayer graphene as an incommensurate superlattice with strong interlayer coupling. Proceedings of the National Academy of Sciences of the United States of America, 2018, 115, 6928-6933.	7.1	169
3	Manipulating the Mixed Perovskite Crystallization Pathway Unveiled by In Situ GIWAXS. Advanced Materials, 2019, 31, e1901284.	21.0	127
4	A brief review of co-doping. Frontiers of Physics, 2016, 11, 1.	5.0	98
5	Strain-Enhanced Doping in Semiconductors: Effects of Dopant Size and Charge State. Physical Review Letters, 2010, 105, 195503.	7.8	97
6	Quantum Electronic Stress: Density-Functional-Theory Formulation and Physical Manifestation. Physical Review Letters, 2012, 109, 055501.	7.8	55
7	New approaches for calculating absolute surface energies of wurtzite (0001)/(0001̄): A study of ZnO and GaN. Journal of Applied Physics, 2016, 119, .	2.5	39
8	Dual-Surfactant Effect to Enhance p-Type Doping in III-V Semiconductor Thin Films. Physical Review Letters, 2008, 101, 196103.	7.8	32
9	Persistent Medium-Range Order and Anomalous Liquid Properties of Al _{1-x} Cu _x Alloys. Physical Review Letters, 2012, 108, 115901.	7.8	29
10	Pseudo-Hydrogen Passivation: A Novel Way to Calculate Absolute Surface Energy of Zinc Blende (111)/(1̄1) Interfaces. Physical Review Letters, 2012, 108, 226105.	7.8	28
11	Atomically Abrupt Liquid-Oxide Interface Stabilized by Self-Regulated Interfacial Defects: The Case of Al ₂ O ₃ /GaAs Interfaces. Physical Review Letters, 2012, 108, 226105.	7.8	28
12	Coulomb Sink: A Novel Coulomb Effect on Coarsening of Metal Nanoclusters on Semiconductor Surfaces. Physical Review Letters, 2004, 93, 106102.	7.8	21
13	Tuning doping site and type by strain: Enhanced n-type doping in Li doped ZnO. Solid State Communications, 2011, 151, 1437-1439.	1.9	21
14	Controlling defects and secondary phases of CZTS by surfactant potassium. Physical Review Materials, 2017, 1, .	2.4	19
15	Enhanced cation-substituted p-type doping in GaP from dual surfactant effects. Journal of Crystal Growth, 2010, 312, 174-179.	1.5	16
16	Realization of stable ferromagnetic order in a topological insulator: Codoping-enhanced magnetism in metal doped Bi ₂ Se ₃ . Physical Review Letters, 2012, 108, 226105.	3.2	14
17	Defect properties of Na and K in Cu ₂ ZnSnS ₄ from hybrid functional calculation. Journal of Applied Physics, 2018, 124, 165701.	2.5	14
18	Hydrogen-surfactant-assisted coherent growth of GaN on ZnO substrate. Physical Review Materials, 2018, 2, .	2.4	14

#	ARTICLE	IF	CITATIONS
19	Missing links towards understanding the equilibrium shapes of hexagonal boron nitride: algorithm, hydrogen passivation, and temperature effects. <i>Nanoscale</i> , 2018, 10, 17683-17690.	5.6	12
20	Twist-driven separation of <i>p</i> -type and <i>n</i> -type dopants in single-crystalline nanowires. <i>National Science Review</i> , 2019, 6, 532-539.	9.5	12
21	New Types of CZTS $\{112\}$ Grain Boundaries: Algorithms to Passivation. <i>Journal of Physical Chemistry C</i> , 2018, 122, 7759-7770.	3.1	11
22	Overcoming doping bottleneck by using surfactant and strain. <i>Frontiers of Materials Science</i> , 2011, 5, 335-341.	2.2	10
23	A brief review of formation energies calculation of surfaces and edges in semiconductors. <i>Journal of Semiconductors</i> , 2020, 41, 061101.	3.7	10
24	Stability of wurtzite semipolar surfaces: Algorithms and practices. <i>Physical Review Materials</i> , 2018, 2, .	2.4	10
25	A two-dimensional ErCu_2 intermetallic compound on Cu(111) with moiré-pattern-modulated electronic structures. <i>Physical Chemistry Chemical Physics</i> , 2020, 22, 1693-1700.	2.8	9
26	Strain tuning of native defect populations: The case of $\text{Cu}_2\text{ZnSn}(\text{S},\text{Se})_4$. <i>APL Materials</i> , 2014, 2, 012110.	5.1	8
27	Surfactant antimony enhanced indium incorporation on InGaN ($\sqrt{10} \times \sqrt{10}$) surface: A DFT study. <i>Journal of Crystal Growth</i> , 2016, 438, 13-18.	1.5	7
28	Stepping Stone Mechanism: Carrier-Free Long-Range Magnetism Mediated by Magnetized Cation States in Quintuple Layer. <i>Chinese Physics Letters</i> , 2018, 35, 017502.	3.3	6
29	Twist-induced preferential distribution of dopants in single-crystalline Si nanowires. <i>Physical Review B</i> , 2019, 100, .	3.2	6
30	Defect calculations using a combined SCAN and hybrid functional in $\hat{\Gamma}_3$ - CsPbI_3 . <i>Physical Chemistry Chemical Physics</i> , 2022, 24, 3420-3428.	2.8	4
31	Absence of quantum anomalous Hall state in transition-metal-doped B_2S_3 .	3.2	3
32	Long-range magnetic order stabilized by acceptors. <i>Physical Review B</i> , 2019, 99, .	3.2	3
33	Determining Equilibrium Shapes of MoS_2 : Modified Algorithm, Edge Reconstructions with S and O, and Temperature Effects. <i>Journal of Physical Chemistry C</i> , 2021, 125, 4828-4835.	3.1	3
34	Kinetic Processes and Surfactant Design of Group I Elements on the CZTS (1×1 to 2×2) Surface. <i>Journal of Physical Chemistry C</i> , 2021, 125, 376-384.	3.1	3
35	Defects properties and vacancy diffusion in $\text{Cu}_2\text{MgSnS}_4$. <i>Journal of Semiconductors</i> , 2022, 43, 022101.	3.7	3
36	Machine-Learning-Assisted Acceleration on High-Symmetry Materials Search: Space Group Predictions from Band Structures. <i>Journal of Physical Chemistry C</i> , 2022, 126, 12264-12273.	3.1	2

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37	Diffusivity and band offset analysis of a graphene interlayer at the back contact of a copper zinc tin sulphide solar cell. <i>Physical Chemistry Chemical Physics</i> , 2021, 23, 3511-3518.	2.8	1
38	One-Pot Shear Synthesis of Gallium, Indium, and Indium-Bismuth Nanofluids: An Experimental and Computational Study. <i>Journal of Nanotechnology in Engineering and Medicine</i> , 2013, 4, .	0.8	0
39	Carrier free long-range magnetism in Mo doped one quintuple layer Bi ₂ Te ₃ and Sb ₂ Te ₃ . <i>Journal of Physics Condensed Matter</i> , 2020, 32, 065801.	1.8	0